FM30N32EQ/T

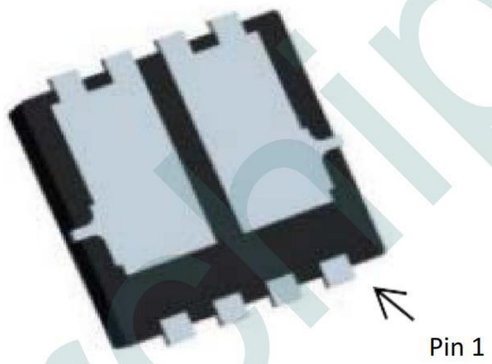
N-Channel Enhancement Mode MOSFET

- 30V,32A
- $R_{DS(ON)}$=6.8mΩ (Typ.) @ V_{GS} =10V
- $R_{DS(ON)}$=9.6mΩ (Typ.) @ V_{GS} =4.5V
- High density cell design for ultra low Rdson
- Fully characterized Avalanche voltage and current

Application

- LCD TV
- Notebook
- Elevator
- Inductive heating Power tools
- Power tools

Package



PDFN3*3

Absolute Maximum Ratings (T_C=25℃ unless otherwise specified)

Symbol	Parameter		Max.	Units
V_{DSS}	Drain-Source Voltage		30	V
V_{GSS}	Gate-Source Voltage		±20	V
I_D	Continuous Drain Current	T_C = 25℃	32	A
		T_C = 100℃	17	A
I_{DM}	Pulsed Drain Current note1		89	A
E_{AS}	Single Pulsed Avalanche Energy note2		86	mJ
P_D	Power Dissipation	T_C = 25℃	28	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		0.22	℃/W
T_J, T_{STG}	Operating and Storage Temperature Range		-50 to +150	℃

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